INTEGRATED CIRCUITS

DATA SHEET

74LVC2G07Buffers with open-drain outputs

Product specification Supersedes data of 2003 Aug 25 2004 Mar 19





Buffers with open-drain outputs

74LVC2G07

FEATURES

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- · High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8B/JESD36 (2.7 V to 3.6 V).
- -24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- SOT363 and SOT457 package
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.

DESCRIPTION

The 74LVC2G07 is a high-performance, low-power, low-voltage, Si-gate CMOS device superior to most advanced CMOS compatible TTL families.

Input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC2G07 provides two non-inverting buffers.

The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PLZ} /t _{PZL}	propagation delay input nA to output nY	$V_{CC} = 1.8 \text{ V}; C_L = 30 \text{ pF}; R_L = 1 \text{ k}\Omega$	3.5	ns
		$V_{CC} = 2.5 \text{ V}; C_L = 30 \text{ pF}; R_L = 500 \Omega$	2.4	ns
		$V_{CC} = 2.7 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	2.3	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	2.6	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	1.5	ns
C _I	input capacitance		2.5	pF
C _{PD}	power dissipation capacitance per gate	V _{CC} = 3.3 V; notes 1 and 2	6.5	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_1 \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

2. The condition is $V_I = GND$ to V_{CC} .

Buffers with open-drain outputs

74LVC2G07

FUNCTION TABLE

See note 1.

INPUT	ОИТРИТ
nA	nY
L	L
Н	Z

Note

1. H = HIGH voltage level;

L = LOW voltage level;

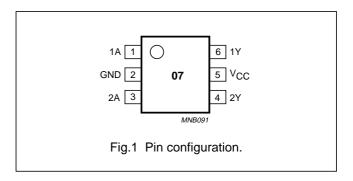
Z = high-impedance OFF-state.

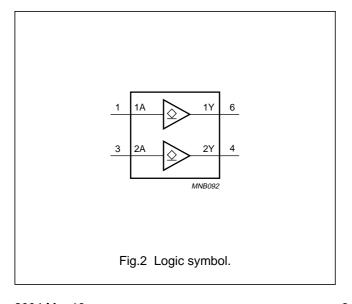
ORDERING INFORMATION

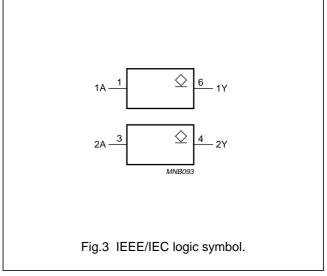
TYPE NUMBER	PACKAGE							
I TPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING		
74LVC2G07GW	-40 °C to +125 °C	6	SC-88	plastic	SOT363	V7		
74LVC2G07GV	–40 °C to +125 °C	6	SC-74	plastic	SOT457	V07		

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	GND	ground (0 V)
3	2A	data input
4	2Y	data output
5	V _{CC}	supply voltage
6	1Y	data output







Buffers with open-drain outputs

74LVC2G07

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	active mode	0	V _{CC}	V
		V _{CC} = 0 V; Power-down mode	0	5.5	V
T _{amb}	operating ambient temperature		-40	+125	°C
t _r , t _f	input rise and fall times	V _{CC} = 1.65 V to 2.7 V	0	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input diode current	V _I < 0 V	_	-50	mA
VI	input voltage	note 1	-0.5	+6.5	V
I _{OK}	output diode current	V _O < 0 V	_	-50	mA
Vo	output voltage	active mode; notes 1 and 2	-0.5	+6.5	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
Io	output source or sink current	V _O = 0 V to 6.5 V	_	50	mA
I _{CC} , I _{GND}	V _{CC} or GND current		_	±100	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	_	300	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

Buffers with open-drain outputs

74LVC2G07

DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

OVMDOL	DADAMETED	TEST COND	ITIONS		TVD	BA A V	
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	UNIT
T _{amb} = -40) °C to +85 °C; note 1		-	1	1	•	•
V _{IH}	HIGH-level input voltage		1.65 to 1.95	$0.65 \times V_{CC}$	_	_	V
			2.3 to 2.7	1.7	_	_	V
			2.7 to 3.6	2.0	_	_	V
			4.5 to 5.5	$0.7 \times V_{CC}$	_	_	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	_	_	$0.35 \times V_{CC}$	V
			2.3 to 2.7	_	_	0.7	V
			2.7 to 3.6	_	_	0.8	V
			4.5 to 5.5	_	_	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		I _O = 100 μA	1.65 to 5.5	_	_	0.1	V
		I _O = 4 mA	1.65	_	_	0.45	V
		$I_O = 8 \text{ mA}$	2.3	_	_	0.3	V
		I _O = 12 mA	2.7	_	_	0.4	V
		I _O = 24 mA	3.0	_	_	0.55	V
		I _O = 32 mA	4.5	_	_	0.55	V
ILI	input leakage current	$V_I = 5.5 \text{ V or GND}$	1.65 to 5.5	_	±0.1	±5	μΑ
I _{OZ}	output OFF-state current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND}$	5.5	_	±0.1	±10	μΑ
I _{off}	power OFF leakage current	V_I or $V_O = 5.5 \text{ V}$	0	_	±0.1	±10	μА
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A	5.5	-	0.1	10	μА
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6 \text{ V};$ $I_O = 0 \text{ A}$	2.3 to 5.5	-	5	500	μА

Buffers with open-drain outputs

74LVC2G07

SAMBOI	DADAMETER	TEST COND	ITIONS	RAINI	TVD	MAY	
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	UNIT
T _{amb} = -40) °C to +125 °C		•	,			•
V _{IH}	HIGH-level input voltage		1.65 to 1.95	$0.65 \times V_{CC}$	_	_	V
			2.3 to 2.7	1.7	_	_	V
			2.7 to 3.6	2.0	_	_	V
			4.5 to 5.5	$0.7 \times V_{CC}$	_	_	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	_	_	$0.35 \times V_{CC}$	V
			2.3 to 2.7	_	_	0.7	V
			2.7 to 3.6	_	_	0.8	V
			4.5 to 5.5	_	_	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}					
		I _O = 100 μA	1.65 to 5.5	_	_	0.1	V
		I _O = 4 mA	1.65	_	_	0.70	V
		I _O = 8 mA	2.3	_	_	0.45	V
		I _O = 12 mA	2.7	_	_	0.60	V
		I _O = 24 mA	3.0	_	_	0.80	V
		I _O = 32 mA	4.5	_	_	0.80	V
ILI	input leakage current	V _I = 5.5 V or GND	1.65 to 5.5	_	_	±20	μΑ
I _{OZ}	output OFF-state current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND}$	5.5	_	_	±10	μΑ
I _{off}	power OFF leakage current	V_I or $V_O = 5.5 \text{ V}$	0	_	_	±20	μΑ
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A	5.5	-	_	40	μΑ
ΔI_{CC}	additional quiescent supply current per pin	$V_{I} = V_{CC} - 0.6 \text{ V};$ $I_{O} = 0 \text{ A}$	2.3 to 5.5	_	_	5000	μΑ

Note

^{1.} All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 $^{\circ}C.$

Buffers with open-drain outputs

74LVC2G07

AC CHARACTERISTICS

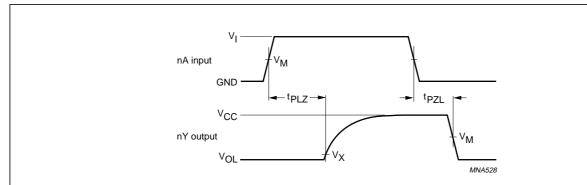
GND = 0 V.

CVMDOL	DADAMETED	TEST CON	DITIONS	MINI	TVD	MAY	LINUT
SYMBOL	PARAMETER	WAVEFORMS	V _{CC} (V)	MIN.	TYP.	MAX.	UNIT
T _{amb} = -40) °C to +85 °C; note 1		•	•			
t _{PLZ} /t _{PZL}	propagation delay input nA to	see Figs 4 and 5	1.65 to 1.95	1.0	3.5	6.7	ns
	output nY		2.3 to 2.7	0.5	2.4	4.3	ns
		2.7	1.0	2.3	4.2	ns	
			3.0 to 3.6	0.5	2.6	3.7	ns
			4.5 to 5.5	0.5	1.5	2.9	ns
$T_{amb} = -40$) °C to +125 °C						
t _{PLZ} /t _{PZL}	propagation delay input nA to	see Figs 4 and 5	1.65 to 1.95	1.0	3.5	8.4	ns
	output nY		2.3 to 2.7	0.5	2.4	5.5	ns
			2.7	1.0	2.3	5.3	ns
			3.0 to 3.6	0.5	2.6	4.7	ns
			4.5 to 5.5	0.5	1.5	3.7	ns

Note

1. All typical values are measured at T_{amb} = 25 °C and at V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

AC WAVEFORMS



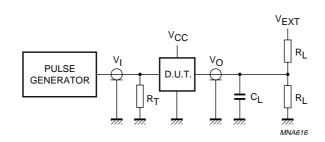
V _{CC}	V _M	V _X	INF	TUT
▼CC	V M	VX	VI	$t_r = t_f$
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{CC}	≤ 2.0 ns
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V _{OL} + 0.15 V	V _{CC}	≤ 2.0 ns
2.7 V	1.5 V	V _{OL} + 0.3 V	2.7 V	≤ 2.5 ns
3.0 V to 3.6 V	1.5 V	V _{OL} + 0.3 V	2.7 V	≤ 2.5 ns
4.5 V to 5.5 V	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	V _{CC}	≤ 2.5 ns

 $\ensuremath{V_{\text{OL}}}$ and $\ensuremath{V_{\text{OH}}}$ are typical output voltage drop that occur with the output load.

Fig.4 Input nA to output nY propagation delays.

Buffers with open-drain outputs

74LVC2G07



V	V	_	В	V _{EXT}
V _{CC}	V _I	CL	R _L	t _{PZL} /t _{PLZ}
1.65 V to 1.95 V	V _{CC}	30 pF	1 kΩ	$2 \times V_{CC}$
2.3 V to 2.7 V	V _{CC}	30 pF	500 Ω	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	50 pF	500 Ω	$2 \times V_{CC}$

Definitions for test circuit:

 R_L = Load resistor.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig.5 Load circuitry for switching times.

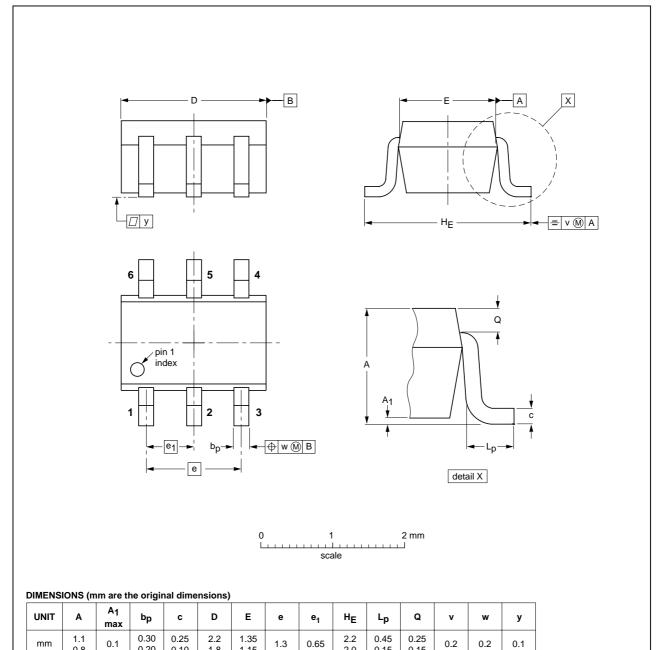
Buffers with open-drain outputs

74LVC2G07

PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT363



OUTLINE		REFERENCES			EUROPEAN		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT363			SC-88			97-02-28	

2004 Mar 19 9

0.10

1.15

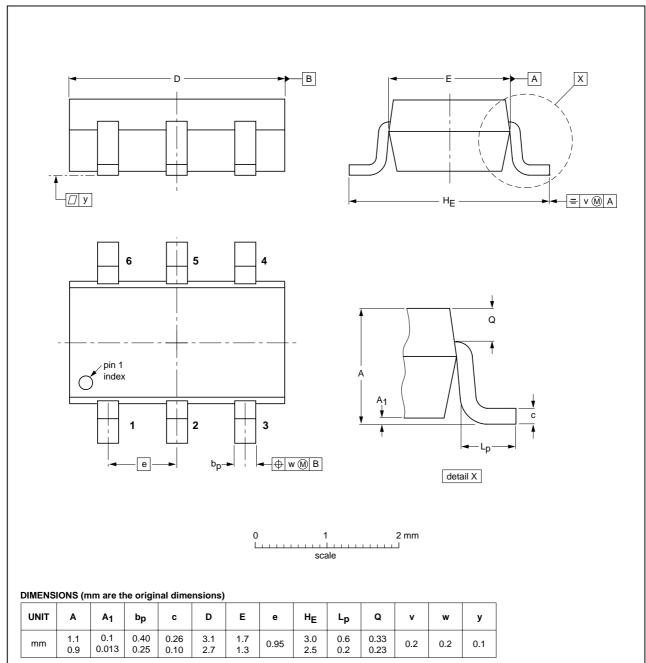
mm

Buffers with open-drain outputs

74LVC2G07

Plastic surface mounted package; 6 leads

SOT457



REFERENCES				EUROPEAN	ISSUE DATE
IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
		SC-74			97-02-28 01-05-04
-	IEC		IEC JEDEC EIAJ	IEC JEDEC EIAJ	IEC JEDEC EIAJ PROJECTION

Buffers with open-drain outputs

74LVC2G07

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

2004 Mar 19

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2004

SCA76

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

R20/02/pp12

Date of release: 2004 Mar 19

Document order number: 9397 750 13011

Let's make things better.

Philips Semiconductors



